

Amendments to the Specification:

Page 1, Paragraph 1, please amend the title as follows:

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE—AND  
FABRICATING METHOD THEREOF

## SEMICONDUCTOR DEVICE AND

### FABRICATING METHOD THEREOF

This application is a DIV of 10/214,693 08/09/02 which is a DIV of 09/120,244 07/22/1998 PAT 6,432,756.

### BACKGROUND OF THE INVENTION

#### 5 1. Field of the Invention:

The present invention disclosed in the specification relates to a method of fabricating a thin film transistor using a crystalline semiconductor film.

#### 10 2. Description of Related Art:

Conventionally, there has been known a thin film transistor (hereinafter, referred to as TFT) using an amorphous silicon film. The transistor is utilized mainly for constituting an active matrix circuit of a liquid crystal display device of an active matrix type.

15 However, according to TFT using an amorphous silicon film, there poses a problem where the operational speed is retarded and a P-channel type one cannot be reduced to practice.

20 The transistor cannot be used in a liquid crystal display device of an active matrix type integrated with a peripheral drive circuit and various integrated circuits cannot be constituted by using such TFT because of such a problem.

There has been known a constitution using a crystalline silicon film as means for resolving the problem.

25 As methods of fabricating a crystalline silicon film, there are classified roughly into a method by heating and a method by irradiation of laser beam.

According to the method by heating, there poses a problem where a glass substrate cannot be utilized since a process at a high temperature as high as 900 °C or higher is needed.

30 In consideration of the fact that a major field of application of TFT is a liquid crystal display device, capability of utilizing a glass substrate as a substrate constitutes a problem with priority.